Vishay Semiconductors

COMPLIANT

Thyristor High Voltage, Surface Mount Phase Control SCR, 16 A



| PRIMARY CHARACTERISTICS | | | | | | | |
|------------------------------------|-------------------------------|--|--|--|--|--|--|
| I _{T(AV)} 10 A | | | | | | | |
| V _{DRM} /V _{RRM} | 800 V, 1200 V | | | | | | |
| V_{TM} | 1.4 V | | | | | | |
| I _{GT} | 60 mA | | | | | | |
| T_J | -40 °C to 125 °C | | | | | | |
| Package | D ² PAK (TO-263AB) | | | | | | |
| Circuit configuration | Single SCR | | | | | | |

FEATURES

 Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C

 Designed and qualified according JEDEC®-JESD 47

JEDEC®-JESD 47

• Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-16TTS..S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

| OUTPUT CURRENT IN TYPICAL APPLICATIONS | | | | | | | | | |
|---|------|------|---|--|--|--|--|--|--|
| APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS | | | | | | | | | |
| NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 μm) copper | 2.5 | 3.5 | | | | | | | |
| Aluminum IMS, R _{thCA} = 15 °C/W | 6.3 | 9.5 | A | | | | | | |
| Aluminum IMS with heatsink, R _{thCA} = 5 °C/W | 14.0 | 18.5 | | | | | | | |

Note

• $T_A = 55$ °C, $T_J = 125$ °C, footprint 300 mm²

| MAJOR RATINGS AND CHARACTERISTICS | | | | | | | | | |
|------------------------------------|------------------------------|-------------|-------|--|--|--|--|--|--|
| PARAMETER | TEST CONDITIONS | VALUES | UNITS | | | | | | |
| I _{T(AV)} | Sinusoidal waveform | 10 | ٨ | | | | | | |
| I _{RMS} | | 16 | Α | | | | | | |
| V _{RRM} /V _{DRM} | | 800 to 1200 | V | | | | | | |
| I _{TSM} | | 200 | A | | | | | | |
| V _T | 10 A, T _J = 25 °C | 1.4 | V | | | | | | |
| dV/dt | | 500 | V/µs | | | | | | |
| dl/dt | | 150 | A/µs | | | | | | |
| TJ | | -40 to +125 | °C | | | | | | |

| VOLTAGE RATINGS | | | | | | | | | |
|-----------------|---|--|---|--|--|--|--|--|--|
| PART NUMBER | V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V | V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V | I _{RRM} /I _{DRM} AT 125 °C mA | | | | | | |
| VS-16TTS08S-M3 | 800 | 800 | 10 | | | | | | |
| VS-16TTS12S-M3 | 1200 | 1200 | 10 | | | | | | |



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| ABSOLUTE MAXIMUM RATINGS | | | | | | | | |
|--|----------------------------------|--|---|------|-----|------------------|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | | | UES | UNITS | | |
| FANAIVIETEN | STWIDOL | | TEST CONDITIONS | | | UNITS | | |
| Maximum average on-state current | I _{T(AV)} | $T_{\rm C} = 98 ^{\circ}{\rm C}, 1$ | 80° conduction, half sine wave | 1 | 0 | | | |
| Maximum RMS on-state current | I _{RMS} | | | 1 | 6 | Α | | |
| Maximum peak, one-cycle, | | 10 ms sine p | ulse, rated V _{RRM} applied | 17 | 70 | _ ^ | | |
| non-repetitive surge current | I _{TSM} | 10 ms sine p | ulse, no voltage reapplied | 20 | 00 | | | |
| Maximum I ² t for fusing | I ² t | 10 ms sine p | ulse, rated V _{RRM} applied | 144 | | A ² s | | |
| Maximum i-t for fusing | 1-1 | 10 ms sine pulse, no voltage reapplied | | | 200 | | | |
| Maximum I ² √t for fusing | I ² √t | t = 0.1 ms to | t = 0.1 ms to 10 ms, no voltage reapplied | | | | | |
| Maximum on-state voltage drop | V_{TM} | 10 A, T _J = 25 | 10 A, T _J = 25 °C | | | V | | |
| On-state slope resistance | r _t | T _{.1} = 125 °C | T 405.00 | | .0 | mΩ | | |
| Threshold voltage | V _{T(TO)} | 1J = 125 C | | 1. | 1 | V | | |
| Maximum reverse and direct leakage current | 1 /1 | $T_J = 25 ^{\circ}\text{C}$ | $V_R = \text{rated } V_{RRM} / V_{DRM}$ | 0. | 5 | | | |
| Maximum reverse and direct leakage current | I _{RM} /I _{DM} | T _J = 125 °C | T _J = 125 °C | | 0 | | | |
| Holding current | I _H | Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C | | | 150 | mA | | |
| Maximum latching current | ΙL | Anode supply = 6 V, resistive load, T _J = 25 °C | | | | | | |
| Maximum rate of rise of off-state voltage | dV/dt | $T_J = T_J$ max. linear to 80 % $V_{DRM} = R_g - k = open$ | | | 500 | | | |
| Maximum rate of rise of turned-on current | dl/dt | | 15 | A/µs | | | | |

| TRIGGERING | | | | | | | | |
|---|--------------------|--|--------|-------|--|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | | | |
| Maximum peak gate power | P _{GM} | | 8.0 | W | | | | |
| Maximum average gate power | P _{G(AV)} | | 2.0 | VV | | | | |
| Maximum peak positive gate current | + I _{GM} | | 1.5 | Α | | | | |
| Maximum peak negative gate voltage | - V _{GM} | | 10 | V | | | | |
| | | Anode supply = 6 V, resistive load, T _J = - 10 °C | 90 | mA | | | | |
| Maximum required DC gate current to trigger | I _{GT} | Anode supply = 6 V, resistive load, T _J = 25 °C | 60 | | | | | |
| | | Anode supply = 6 V, resistive load, T _J = 125 °C | 35 | | | | | |
| | | Anode supply = 6 V, resistive load, T _J = - 10 °C | 3.0 | | | | | |
| Maximum required DC gate voltage to trigger | V_{GT} | Anode supply = 6 V, resistive load, T _J = 25 °C | 2.0 | V | | | | |
| | | Anode supply = 6 V, resistive load, T _J = 125 °C | 1.0 | V | | | | |
| Maximum DC gate voltage not to trigger | | T 105 °C V Detect value | 0.25 | | | | | |
| Maximum DC gate current not to trigger | I_{GD} | T _J = 125 °C, V _{DRM} = Rated value | 2.0 | mA | | | | |

| SWITCHING | | | | | | | |
|-------------------------------|-----------------|--------------------------|--------|-------|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | | |
| Typical turn-on time | t _{gt} | T _J = 25 °C | 0.9 | | | | |
| Typical reverse recovery time | t _{rr} | T _{.1} = 125 °C | 4 | μs | | | |
| Typical turn-off time | t _q | 1 _J = 125 G | 110 | | | | |

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| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | | | |
|---|-----------------------------------|--|-------------|-------|--|--|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | | | | |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | -40 to +125 | °C | | | | | |
| Maximum thermal resistance, junction to case | R _{thJC} | DC operation | 1.3 | °C/W | | | | | |
| Typical thermal resistance, junction to ambient | R _{thJA} | PCB mount (1) | 40 | C/VV | | | | | |
| Approximate weight | | | 2 | g | | | | | |
| Approximate weight | | | 0.07 | oz. | | | | | |
| Marking device | | Case style D ² PAK (TO-263AB) | 16TTS08S | | | | | | |
| ividi kilig device | | Case style D-FAR (10-203AB) | 16TTS12S | | | | | | |

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994

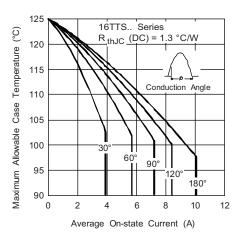


Fig. 1 - Current Rating Characteristics

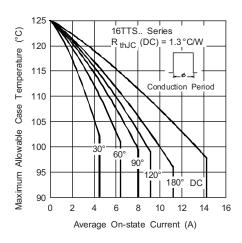


Fig. 2 - Current Rating Characteristics

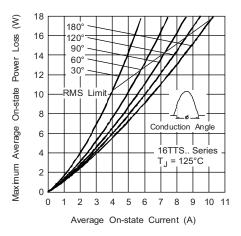


Fig. 3 - On-State Power Loss Characteristics

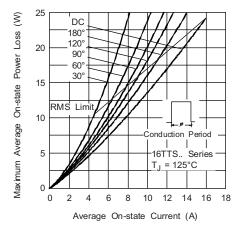


Fig. 4 - On-State Power Loss Characteristics

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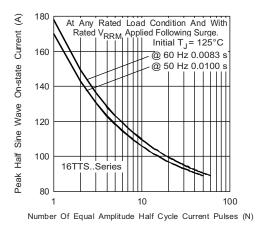


Fig. 5 - Maximum Non-Repetitive Surge Current

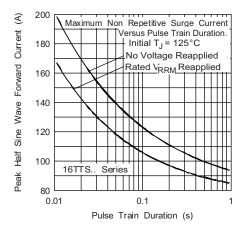


Fig. 6 - Maximum Non-Repetitive Surge Current

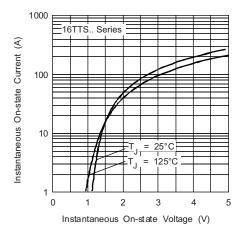


Fig. 7 - On-State Voltage Drop Characteristics

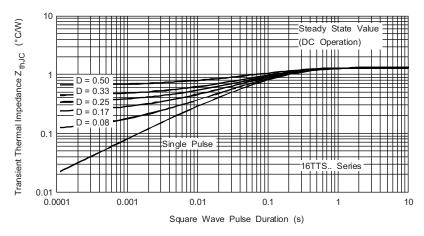


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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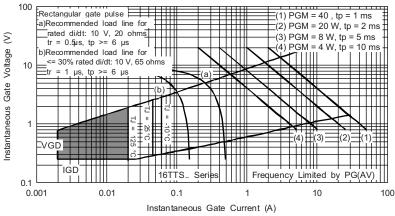
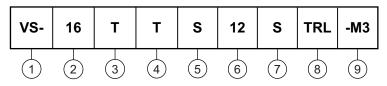


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Current rating
- Circuit configuration:
 - T = single thyristor
- 4 Package:
 - $T = D^2PAK (TO-263AB)$
- 5 Type of silicon:
 - S = standard recovery rectifier
- Voltage rating: voltage code x 100 = V_{RRM} 08 = 800 V 12 = 1200 V
- 7 S = surface mountable
- 8 • None = tube
 - TRL = tape and reel (left oriented)
 - TRR = tape and reel (right oriented)
- 9 -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

| ORDERING INFORMATION (Example) | | | | | | | | | |
|--------------------------------|------------------|------------------------|--------------------------|--|--|--|--|--|--|
| PREFERRED P/N | QUANTITY PER T/R | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION | | | | | | |
| VS-16TTS08S-M3 | 50 | 1000 | Antistatic plastic tubes | | | | | | |
| VS-16TTS08STRR-M3 | 800 | 800 | 13" diameter reel | | | | | | |
| VS-16TTS08STRL-M3 | 800 | 800 | 13" diameter reel | | | | | | |
| VS-16TTS12S-M3 | 50 | 1000 | Antistatic plastic tubes | | | | | | |
| VS-16TTS12STRR-M3 | 800 | 800 | 13" diameter reel | | | | | | |
| VS-16TTS12STRL-M3 | 800 | 800 | 13" diameter reel | | | | | | |

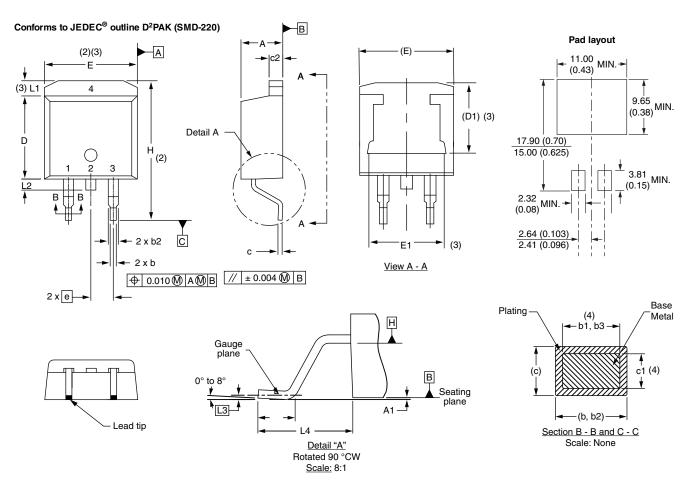
| LINKS TO RELATED DOCUMENTS | | | | | | |
|--|--------------------------|--|--|--|--|--|
| Dimensions <u>www.vishay.com/doc?96164</u> | | | | | | |
| Part marking information | www.vishay.com/doc?95444 | | | | | |
| Packaging information | www.vishay.com/doc?96424 | | | | | |
| SPICE model | www.vishay.com/doc?96772 | | | | | |



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D²PAK

DIMENSIONS in millimeters and inches



| SYMBOL | MILLIM | ETERS | INC | HES | NOTES | SYMBOL | MILLIM | ETERS | INC | HES | NOTES | |
|---------|--------|-------|-------|-------|-------|--------|----------|-------|-------|-------|-------|-------|
| STWIBOL | MIN. | MAX. | MIN. | MAX. | NOTES | NOTES | STIVIBUL | MIN. | MAX. | MIN. | MAX. | NOTES |
| Α | 4.06 | 4.83 | 0.160 | 0.190 | | | D1 | 6.86 | 8.00 | 0.270 | 0.315 | 3 |
| A1 | 0.00 | 0.254 | 0.000 | 0.010 | | | E | 9.65 | 10.67 | 0.380 | 0.420 | 2, 3 |
| b | 0.51 | 0.99 | 0.020 | 0.039 | | | E1 | 7.90 | 8.80 | 0.311 | 0.346 | 3 |
| b1 | 0.51 | 0.89 | 0.020 | 0.035 | 4 | | е | 2.54 | BSC | 0.100 | BSC | |
| b2 | 1.14 | 1.78 | 0.045 | 0.070 | | | Н | 14.61 | 15.88 | 0.575 | 0.625 | |
| b3 | 1.14 | 1.73 | 0.045 | 0.068 | 4 | | L | 1.78 | 2.79 | 0.070 | 0.110 | |
| С | 0.38 | 0.74 | 0.015 | 0.029 | | | L1 | - | 1.65 | - | 0.066 | 3 |
| c1 | 0.38 | 0.58 | 0.015 | 0.023 | 4 | | L2 | 1.27 | 1.78 | 0.050 | 0.070 | |
| c2 | 1.14 | 1.65 | 0.045 | 0.065 | | | L3 | 0.25 | BSC | 0.010 | BSC | |
| D | 8.51 | 9.65 | 0.335 | 0.380 | 2 | | L4 | 4.78 | 5.28 | 0.188 | 0.208 | |

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

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